

## 1. General description

WSJM80R200X is a high voltage N-channel MOSFET in TO220F package, which utilizes the advanced super-junction technology to provide superior FOM  $R_{DS(on)} \cdot Q_g$  among silicon based MOSFETs. It is particularly suitable for applications require extreme high efficiency and power density.



## 2. Features and benefits

- Superior FOM  $R_{DS(on)} \cdot Q_g$
- Extremely low switching loss
- 100% avalanche tested

## 3. Applications

- Solar
- LED power
- Flyback topologies for high efficiency power supplies

## 4. Quick reference data

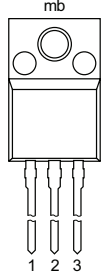
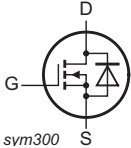
Table 1. Quick reference data

Table 11: Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V <sub>DS</sub>	drain-source voltage			800			V
V <sub>GS</sub>	gate-source voltage			±30			V
I <sub>D</sub>	continuous drain current	T <sub>h</sub> = 25 °C	[1]	22			A
P <sub>tot</sub>	power dissipation	T <sub>h</sub> = 25 °C		37			W
T <sub>j</sub>	junction temperature			-55 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10.5 A		-	180	200	mΩ
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10.5 A; V <sub>DS</sub> = 640 V; V <sub>GS</sub> = 10 V		-	52	-	nC
E <sub>OSS</sub>	coss stored energy	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 0 to 640 V		-	11	-	μJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WSJM80R200X	TO220F	WSJM80R200XQ	Tube	50	SOT186A	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
WSJM80R200X	WSJM 80R200X

8. Limiting values

Table 5. Limiting values  
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage			800	V
$V_{GS}$	gate-source voltage			$\pm 30$	V
$I_D$	continuous drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	[1]	22	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$	[1]	14	A
$I_{DM}$	pulsed drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$		88	A
$P_{tot}$	power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$		37	W
$E_{AS}$	single pulse drain-to-source avalanche	$I_{AS} = 3.5\text{ A}$ ; $R_{GS} = 25\text{ }\Omega$ ; $V_{DD} = 50\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$		61	mJ
$E_{AR}$	repetitive avalanche energy	$I_{AS} = 3.5\text{ A}$ ; $R_{GS} = 25\text{ }\Omega$ ; $V_{DD} = 50\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$		0.13	mJ
$I_{AS}$	avalanche current, single pulse			3.5	A
dv/dt	MOSFET dv/dt ruggedness			50	V/ns
dv/dt	reverse diode dv/dt			15	V/ns
dI <sub>p</sub> /dt	maximum diode commutation speed			50	A/ $\mu$ s
$T_{stg}$	storage temperature			-55 to 150	$^{\circ}\text{C}$
$T_j$	junction temperature			-55 to 150	$^{\circ}\text{C}$

[1] Limited by maximum junction temperature, equivalent to TO220.

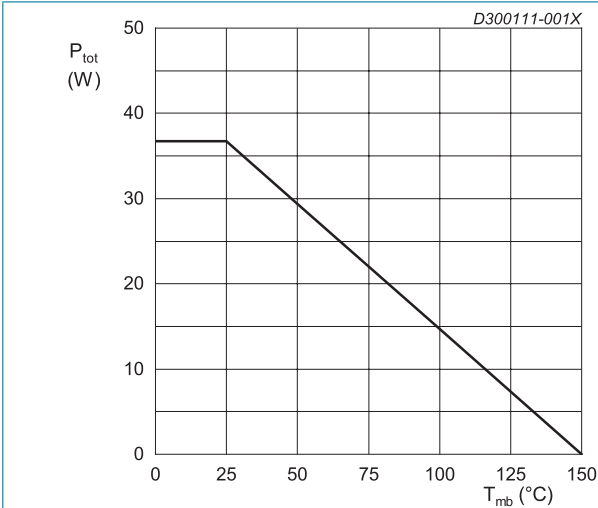


Fig. 1. Total power dissipation as a function of heatsink temperature

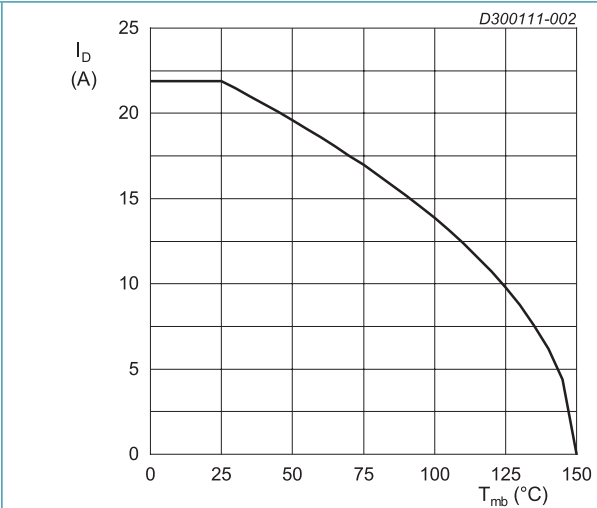


Fig. 2. Continuous Drain Current as a function of heatsink temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink			-	2.6	3.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

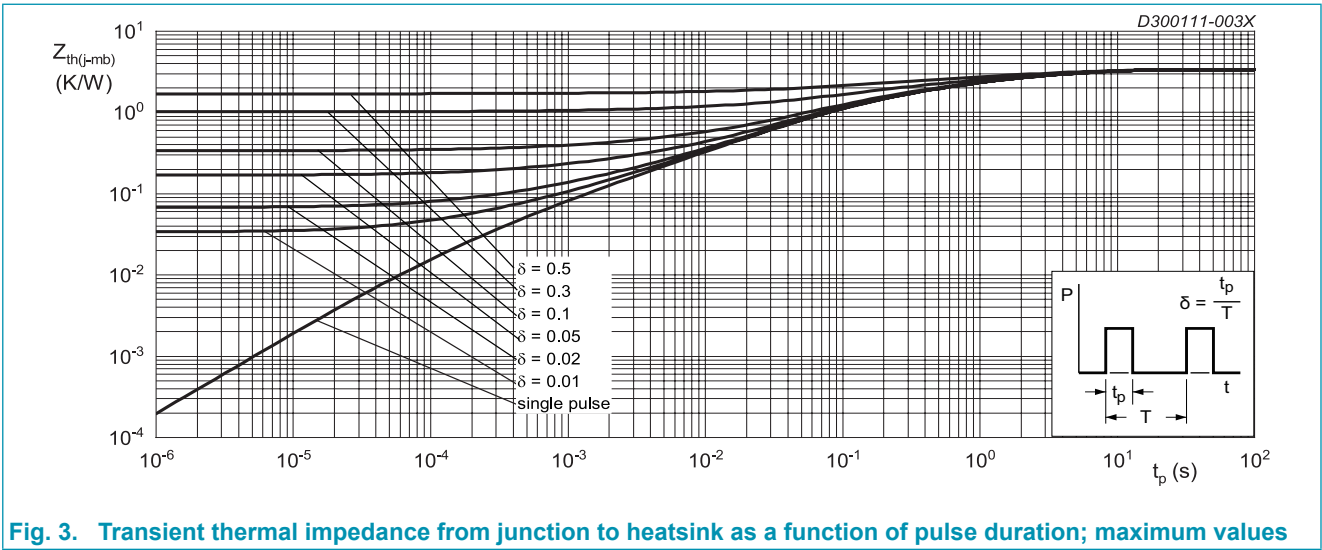


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values

## 10. Characteristics

**Table 7. Characteristics**

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V		800	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub>		2.5	-	4.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 800 V; V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> = 800 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C		-	-	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = ±30 V; V <sub>DS</sub> = 0 V		-	-	±100	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10.5 A		-	180	200	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz		-	1.8	-	Ω
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10.5 A; V <sub>DS</sub> = 640 V; V <sub>GS</sub> = 10 V		-	52	-	nC
Q <sub>GS</sub>	gate-source charge			-	12	-	nC
Q <sub>GD</sub>	gate-drain charge			-	19	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 640 V; V <sub>GS</sub> = 0 V; f = 250 kHz		-	2413	-	pF
C <sub>oss</sub>	output capacitance			-	46	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	0.7	-	pF
C <sub>o(er)</sub>	effective output capacitance, energy related	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 0 to 640 V		-	52	-	pF
C <sub>o(tr)</sub>	effective output capacitance, time related			-	221	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 400 V; V <sub>GS</sub> = 10 V; R <sub>G</sub> = 3 Ω; I <sub>D</sub> = 10.5 A		-	16	-	ns
t <sub>r</sub>	rise time			-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	45	-	ns
t <sub>f</sub>	fall time			-	8.5	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	V <sub>GS</sub> = 0 V; I <sub>S</sub> = 10.5 A		-	0.8	1.1	V
I <sub>S</sub>	body-diode continuous current	T <sub>h</sub> = 25 °C		-	-	22	A
t <sub>rr</sub>	reverse recovery time	V <sub>R</sub> = 400 V; I <sub>F</sub> = 10.5 A; dI <sub>F</sub> /dt = 100 A/μs		-	377	-	ns
Q <sub>rr</sub>	reverse recovered charge			-	6.4	-	μC
I <sub>rrm</sub>	reverse recovery current			-	31	-	A

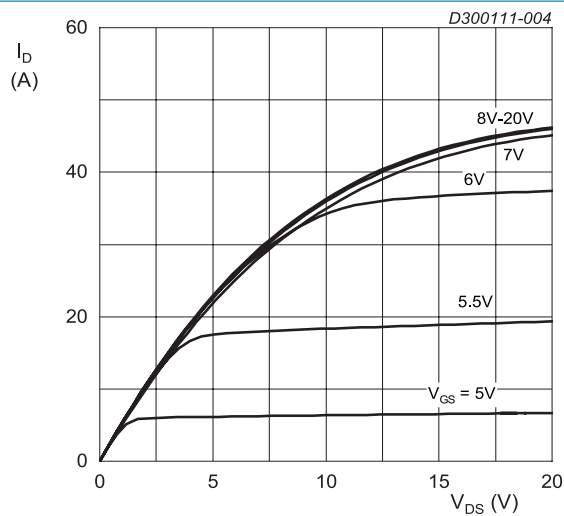
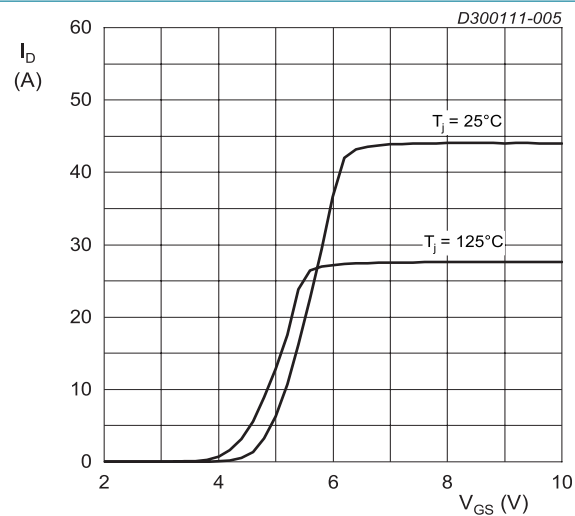
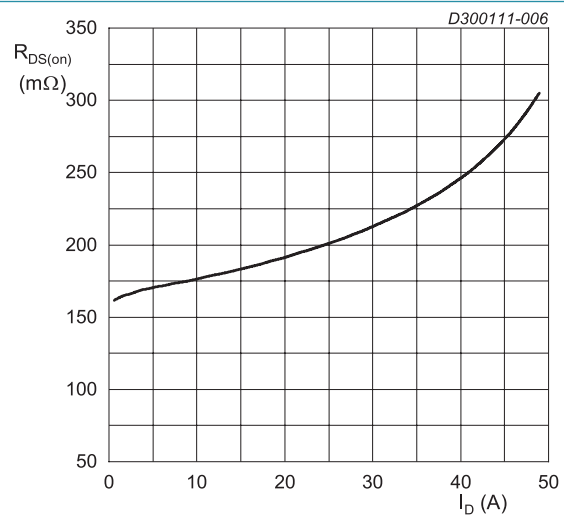


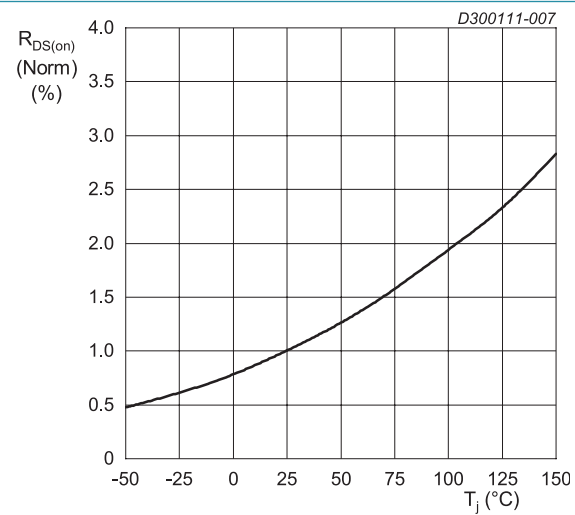
Fig. 4. Drain current as a function of drain-source voltage; typical values



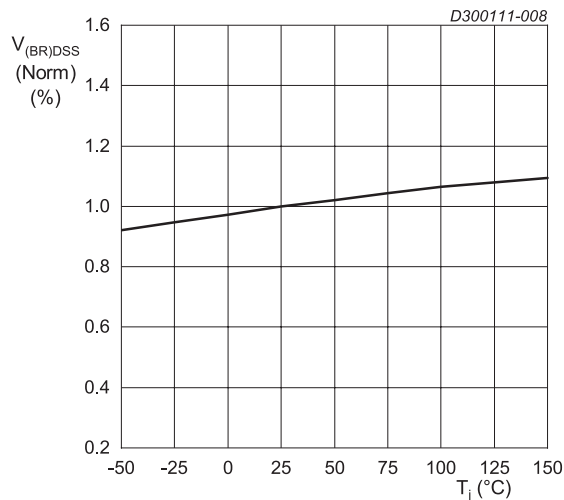
$V_{DS} = 20\text{ V}$   
Fig. 5. Drain current as a function of gate-source voltage; typical values



$V_{GS} = 10\text{ V}$   
Fig. 6. Drain-source on-state resistance as a function of drain current; typical values

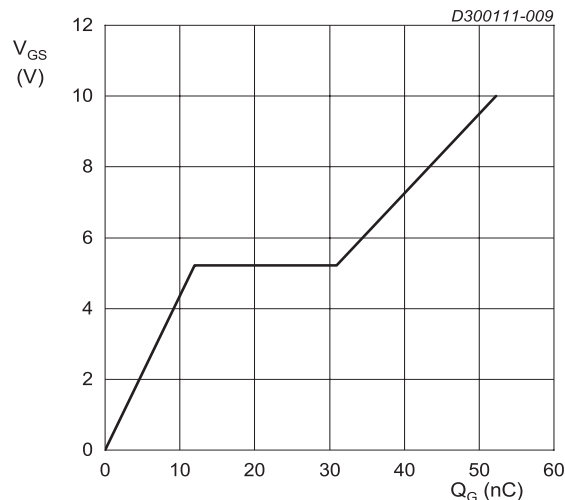


$V_{GS} = 10\text{ V}$ ;  $I_D = 10.5\text{ A}$   
Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature



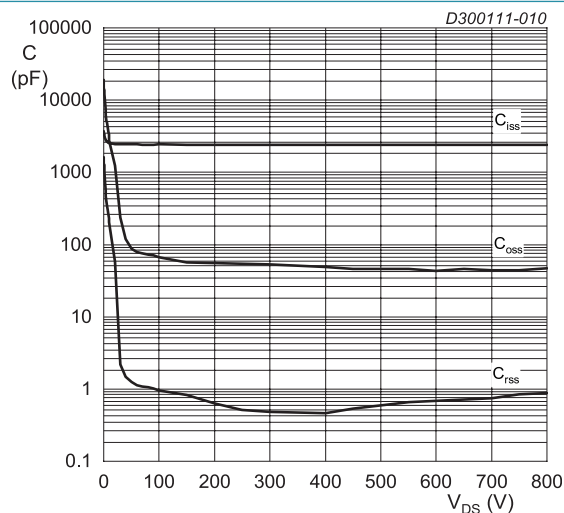
$I_D = 250 \mu A$

Fig. 8. Normalized drain-source breakdown voltage as a function of junction temperature



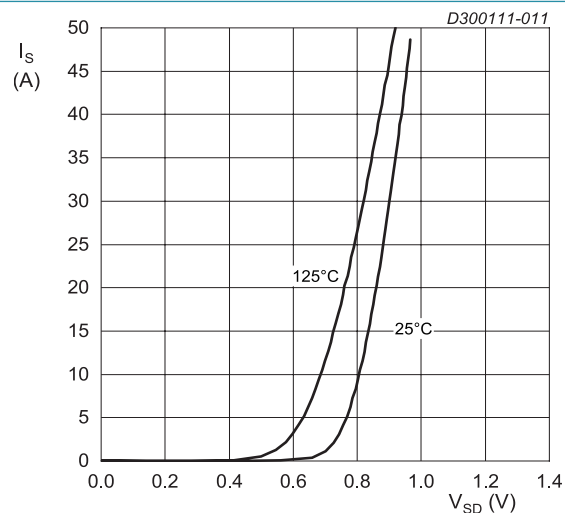
$I_D = 10.5 A$ ;  $V_{DS} = 640 V$

Fig. 9. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 V$ ;  $f = 250 kHz$

Fig 10. Capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 V$

Fig 11. Source current as a function of source-drain voltage; typical values

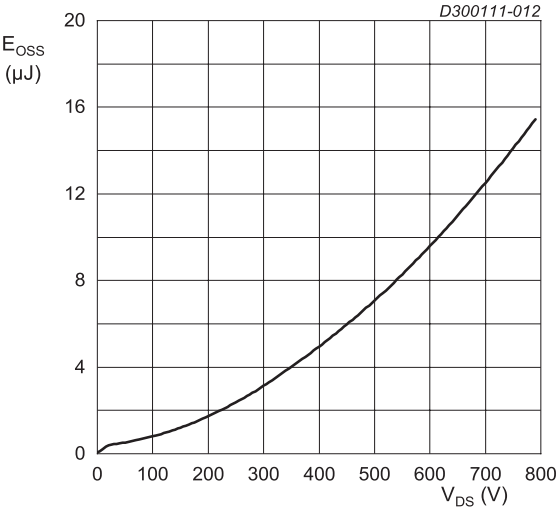
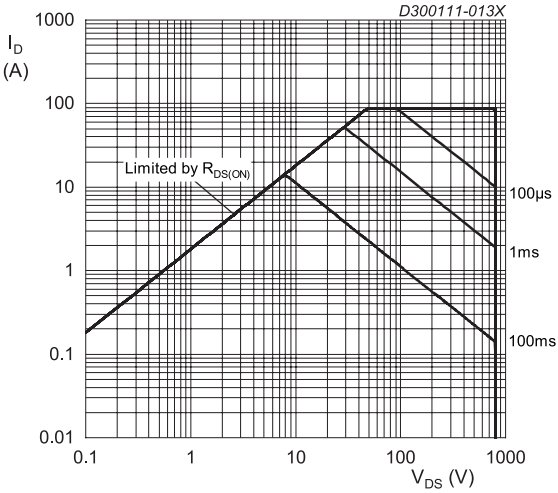


Fig. 12. Output capacitance stored energy as a function of drain-source voltage



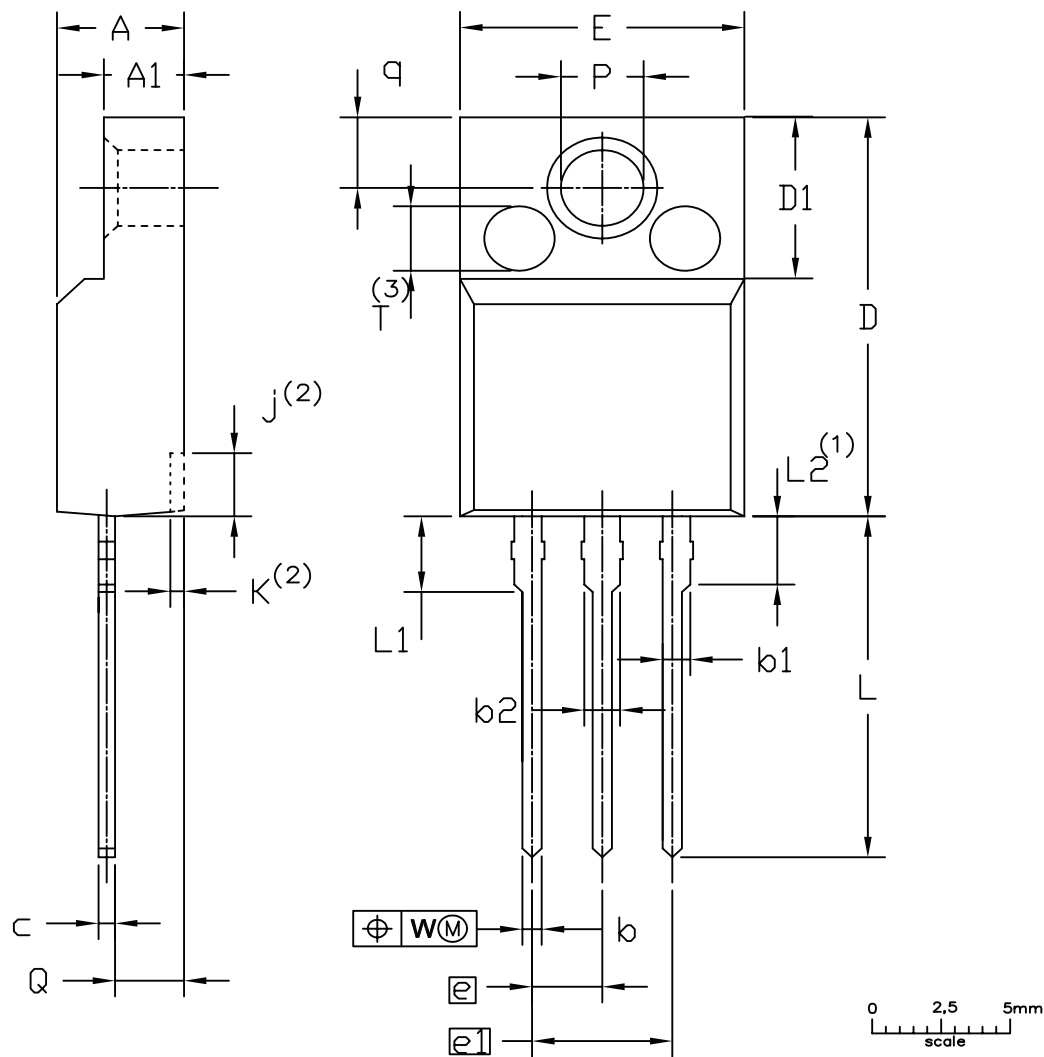
$T_h = 25\text{ }^{\circ}\text{C}$   
Fig. 13. Safe operating area



11. Package outline

Plastic single-ended package;isolated heatsink mounted;1 mounting hole;3-lead TO-220 "full pack"

SOT186A



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	e <sub>1</sub>	j <sup>(2)</sup>	k <sup>(2)</sup>	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	Q	q	W	T <sup>(3)</sup>
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3			2.7	0.6	14.4	3.30		3.2	2.6	3.0		
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7	2.54	5.08	1.7	0.4	13.5	2.79	3	3.0	2.3	2.6	0.4	2.5

- Notes
- 1. Terminal dimensions within this zone are uncontrolled
  - 2. Dot lines area designs may vary
  - 3. Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3 LEADS TO220F				2013-11-14

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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